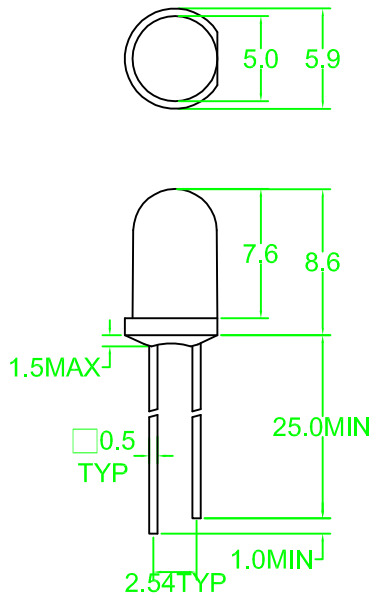


Package Dimension



Note : 1.All dimension are in millimeter tolerance is  $\pm 0.25\text{mm}$  unless otherwise noted.  
2.Specifications are subject to change without notice

Features

- High radiant intensity
- Suitable for pulsed applications
- Low average degradation

Description

The LIR333X series are high power solution grown epitaxial Gallium Arsenide infrared emitting diodes encapsulated in blue transparent or water clear plastic T-1 3/4 package individually

• Electrical Optical Characteristics (At 25°C)

PARAMETER	SYMBOL	PART NO	MIN	TYP	MAX	UNIT	TEST CONDITION
Radiant Intensity	Le	LIR3333	6.0	10		mW/sr	IF=20mA
		LIR3331	6.0	10			
Aperture Radiant Incidence	Ee	LIR3333	0.9	1.5		mW/cm <sup>2</sup>	
		LIR3331	0.9	1.5			
Peak Emission Wavelength	$\lambda$ peak			940		nm	IF=20mA
Spectral Line Half Width	$\Delta \lambda$			50		nm	IF=20mA
Forward Voltage	VF			1.2	1.6	V	IF=20mA
Reverse Current	IR				100	$\mu$ A	VR=5V
Viewing Angle	$2\theta$ 1/2			20		deg	

• Absolute Maximum Rating (Ta=25°C)

PARAMETER	MAXIMUM	UNIT
Power Dissipation	100	mW
Peak Forward Current (300pps, 1 $\mu$ s Pulse)	3	A
Continuous Forward Current	50	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C TO +100°C	
Storage Temperature Range	-55°C TO +100°C	
Lead Soldering Temperature 1.6mm(0.036") Form	260°C For 5 Seconds	